

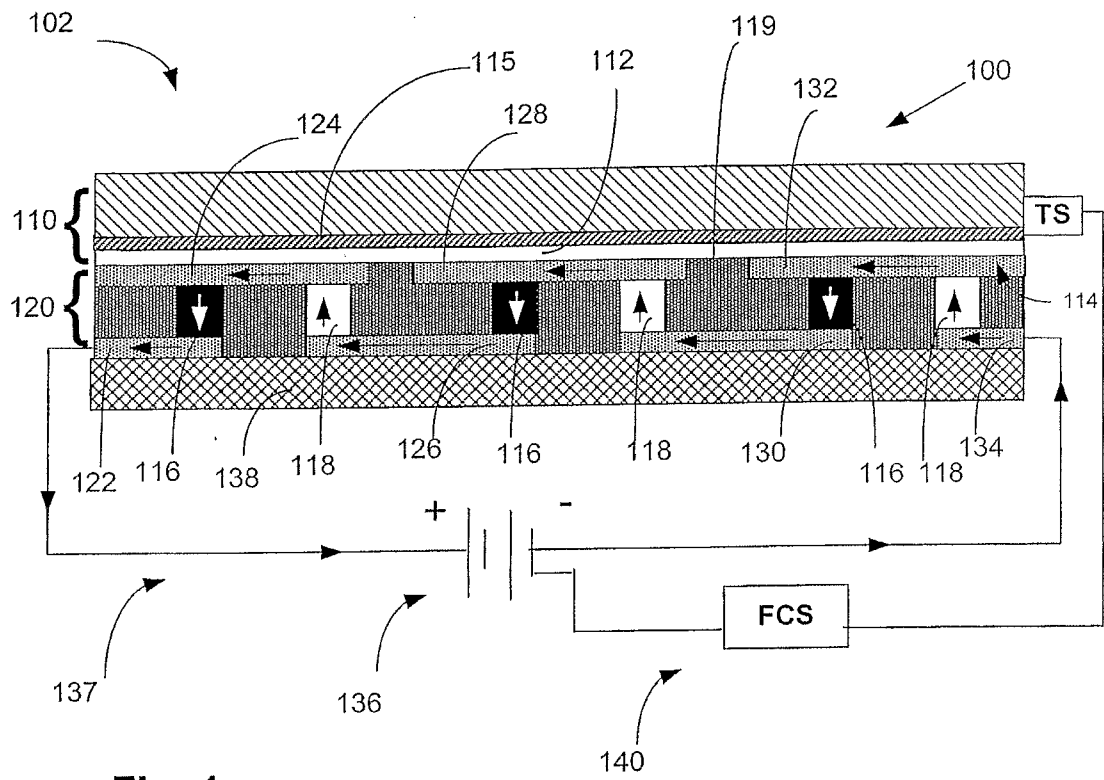


Fig. 1

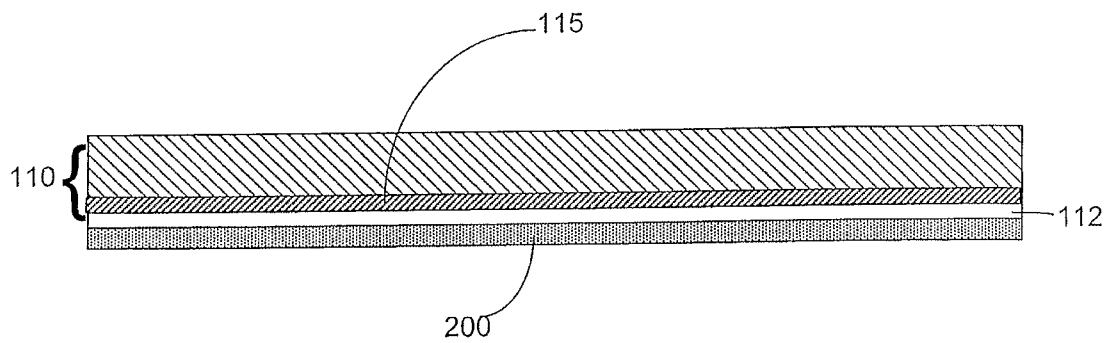


Fig. 2

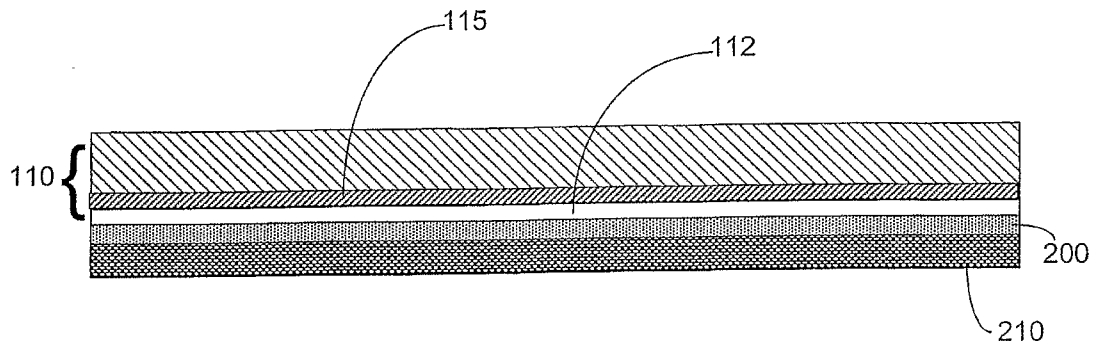


Fig. 3a

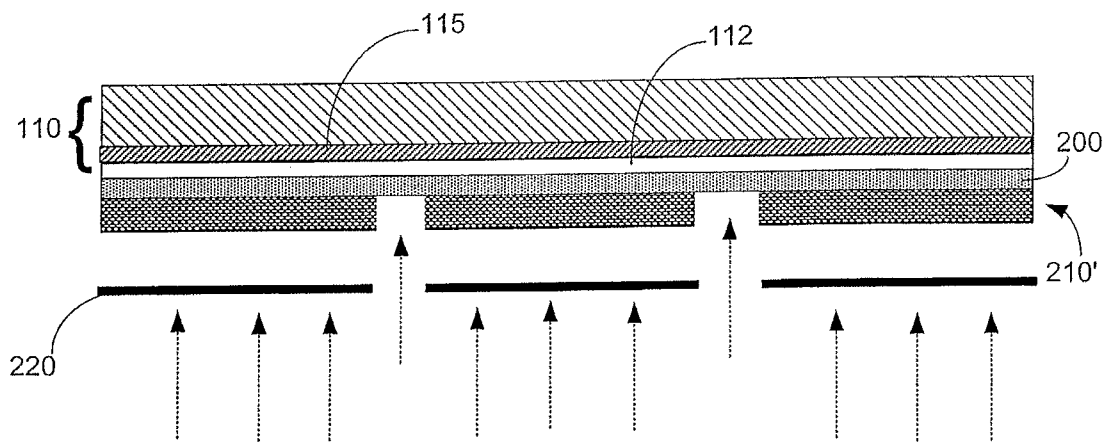


Fig. 3b

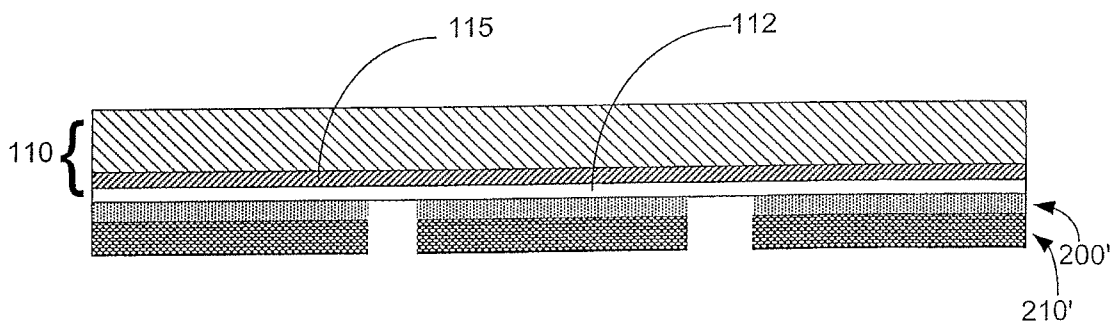


Fig. 3c

A cross-sectional view of a semiconductor device 200'. The device consists of a substrate 230, a patterned layer 200, and a top layer 110. The top layer 110 includes a thin layer 112 and a thicker layer 115.

Fig. 4

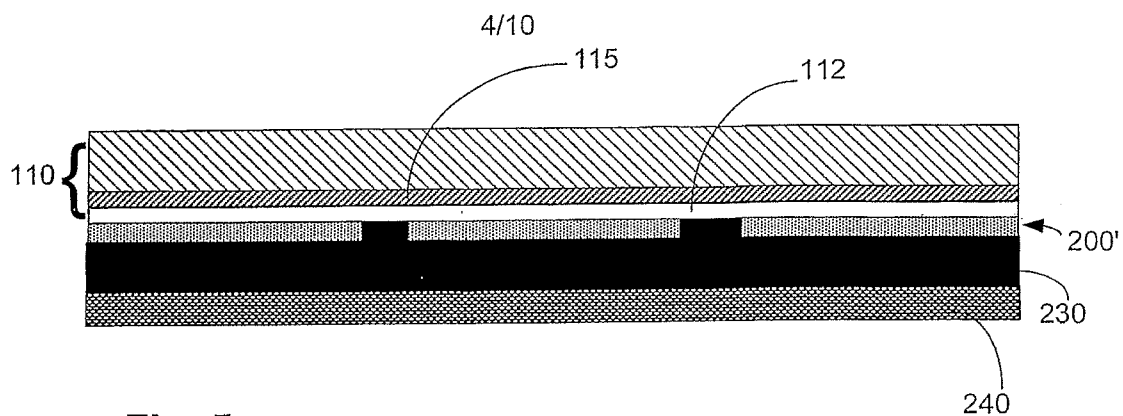


Fig. 5a

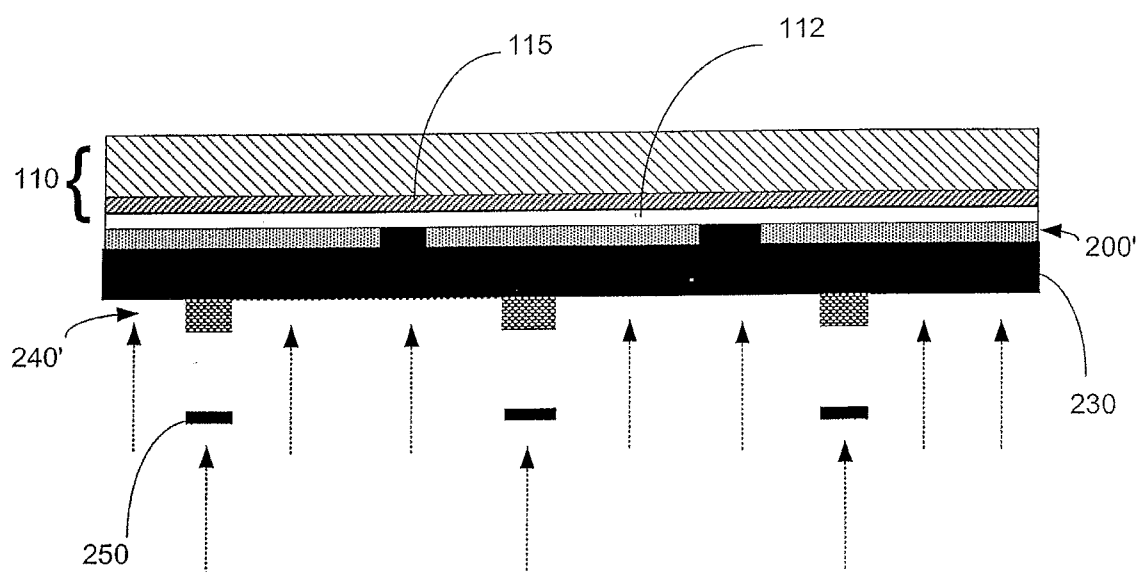


Fig. 5b

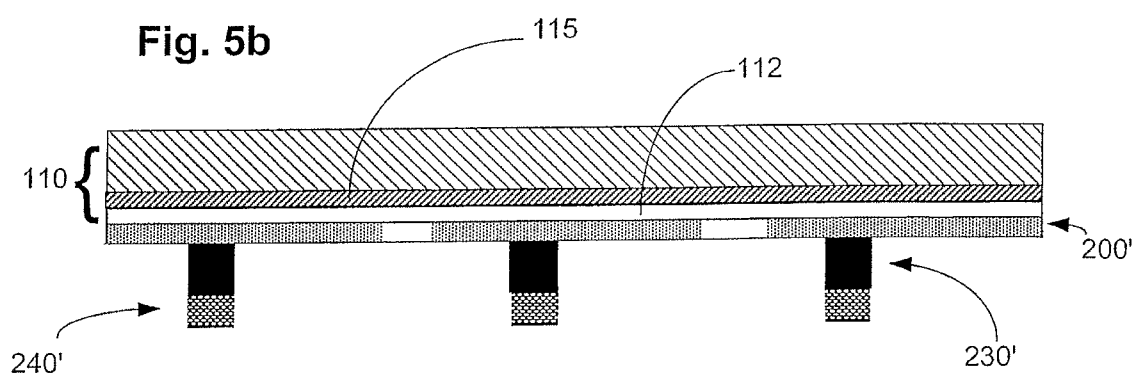


Fig. 5c

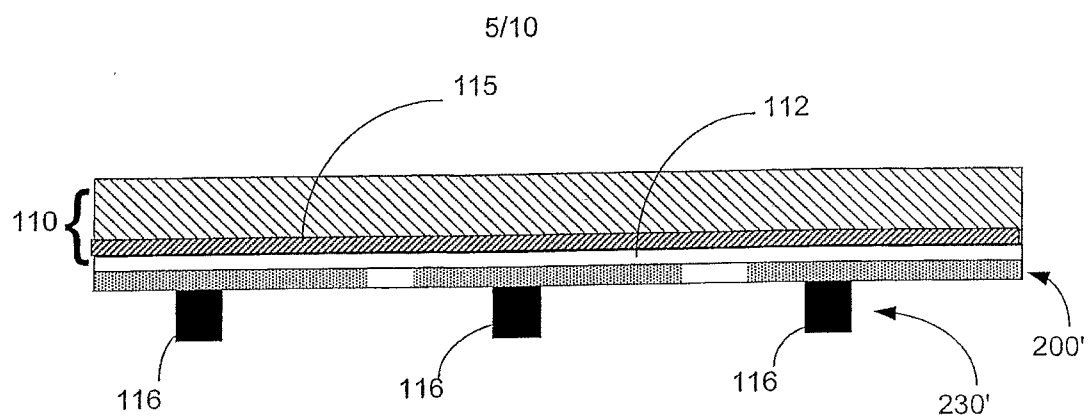


Fig. 5d

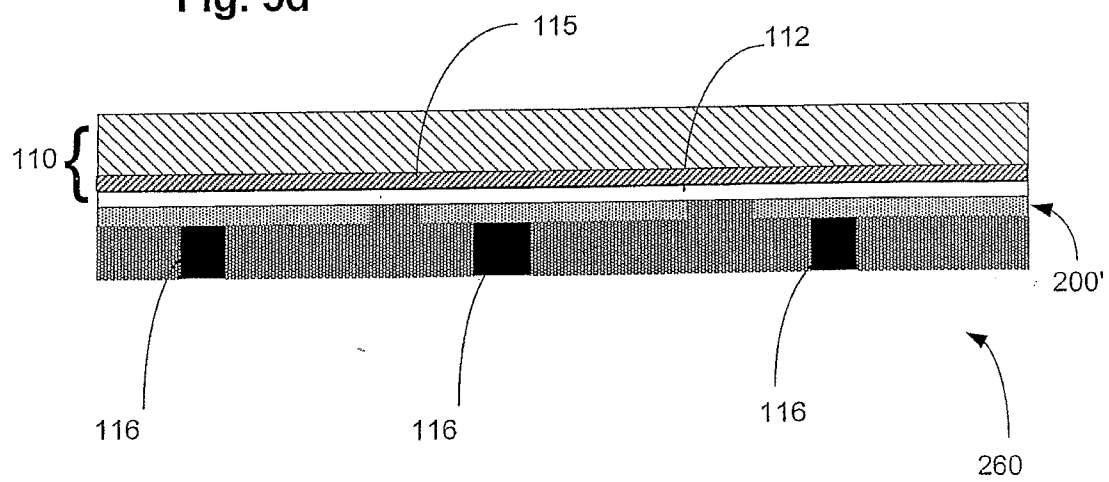


Fig. 6

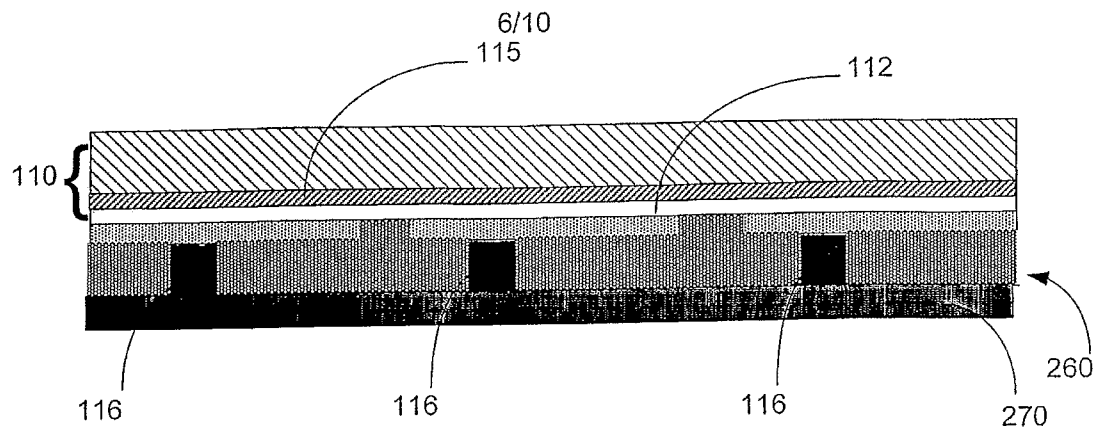


Fig. 7a

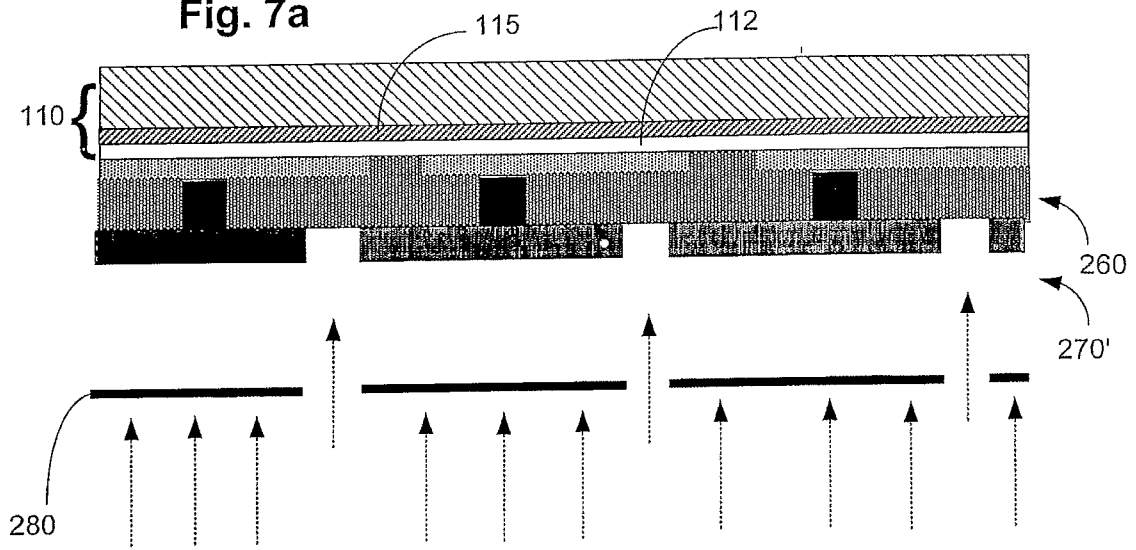


Fig. 7b

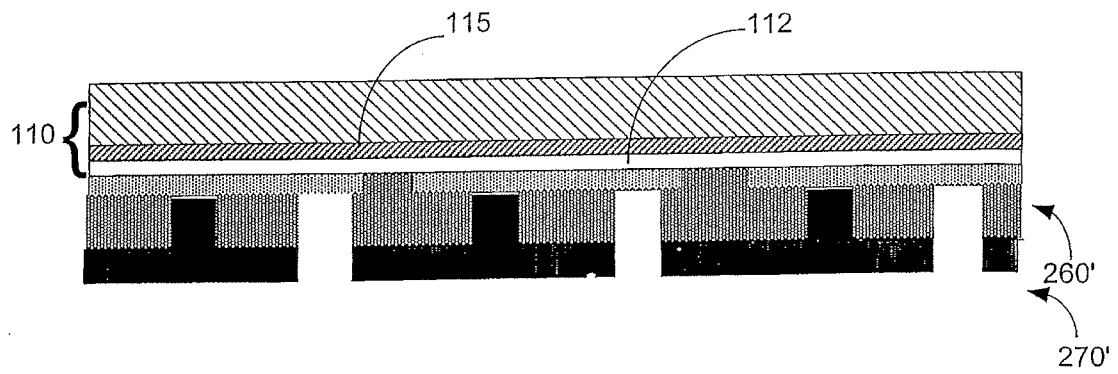
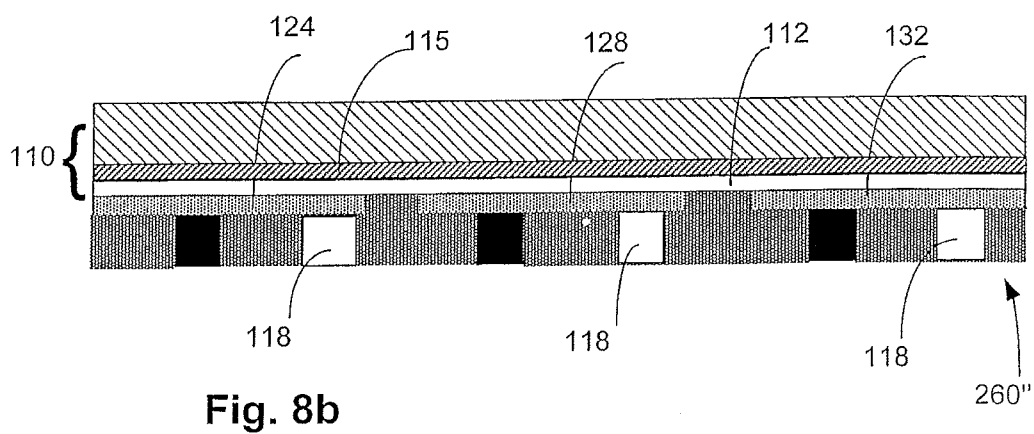
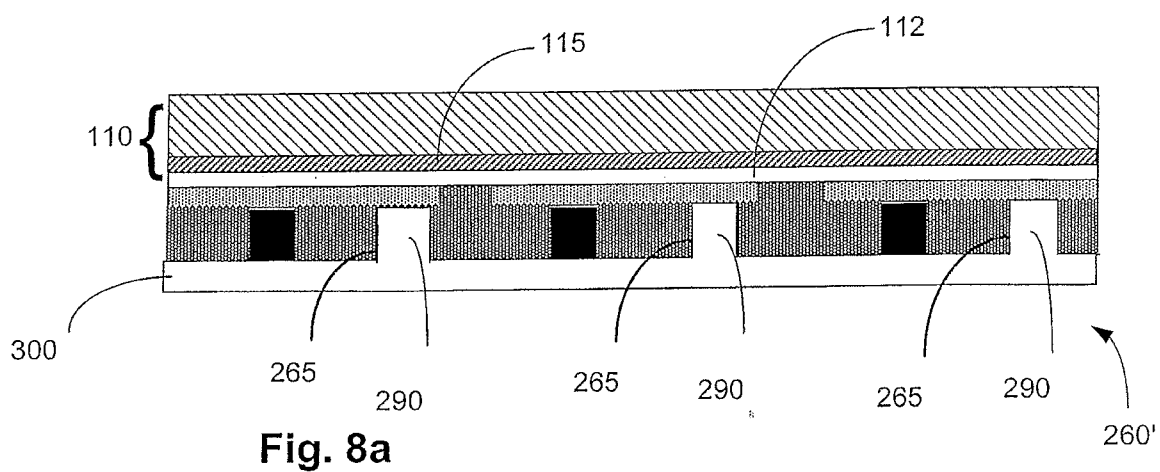
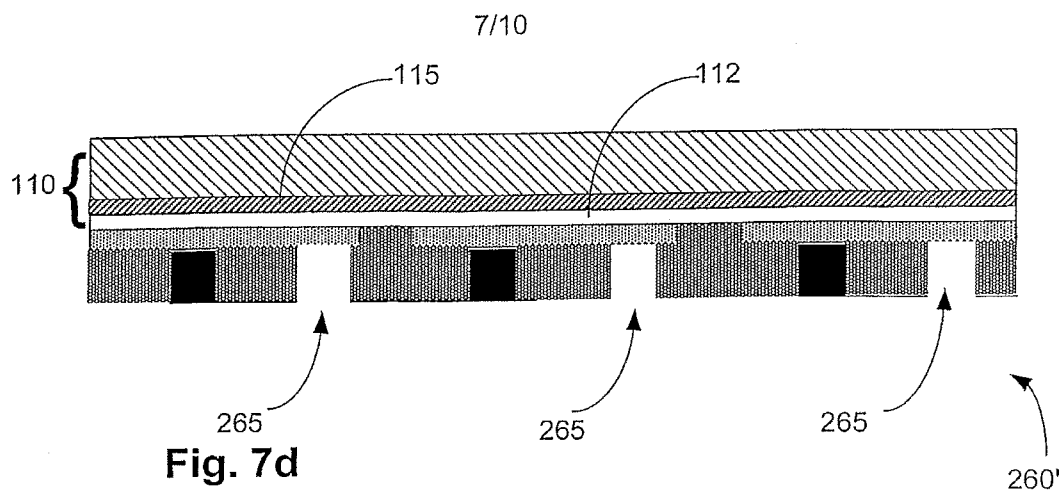


Fig. 7c



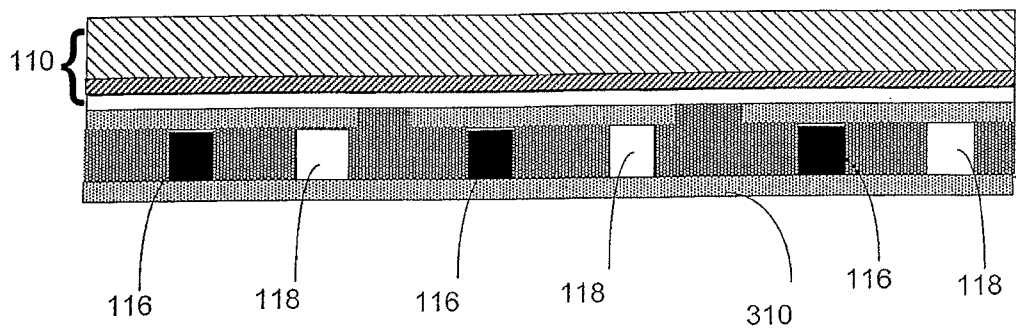


Fig. 9

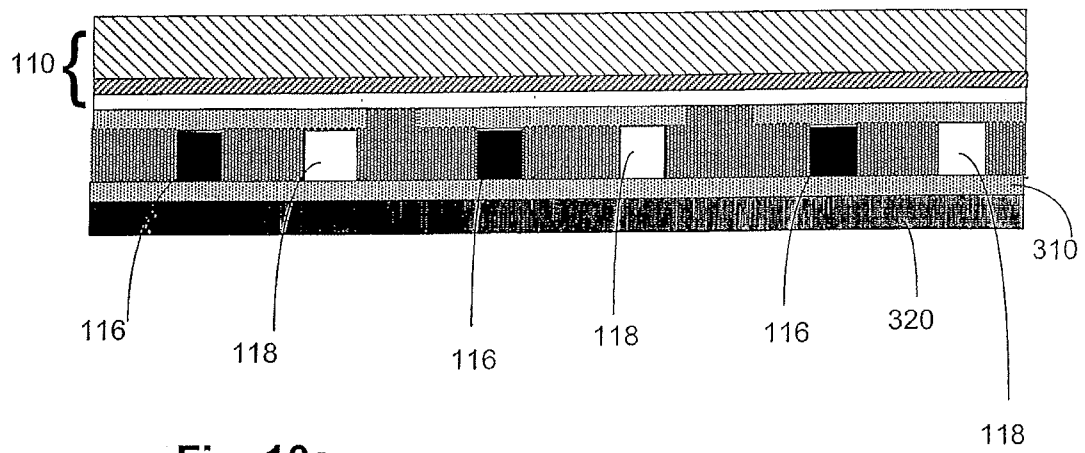


Fig. 10a

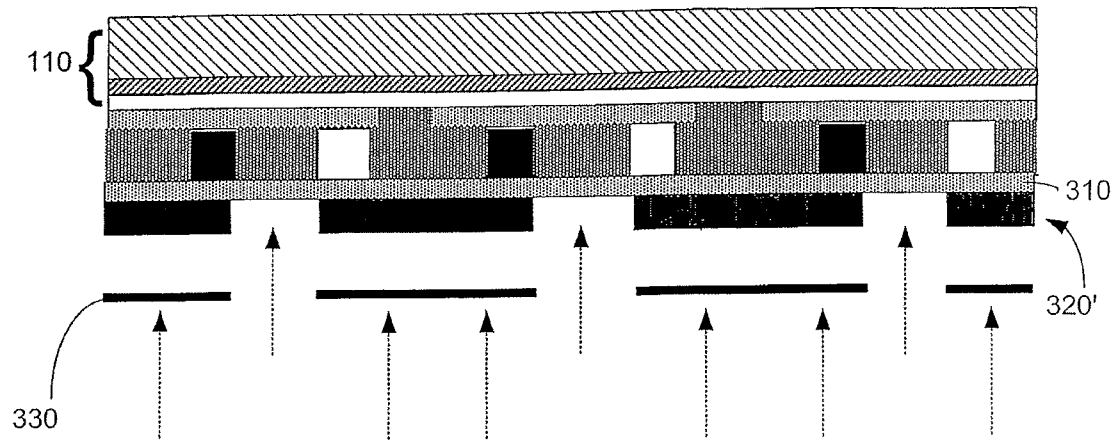


Fig. 10b

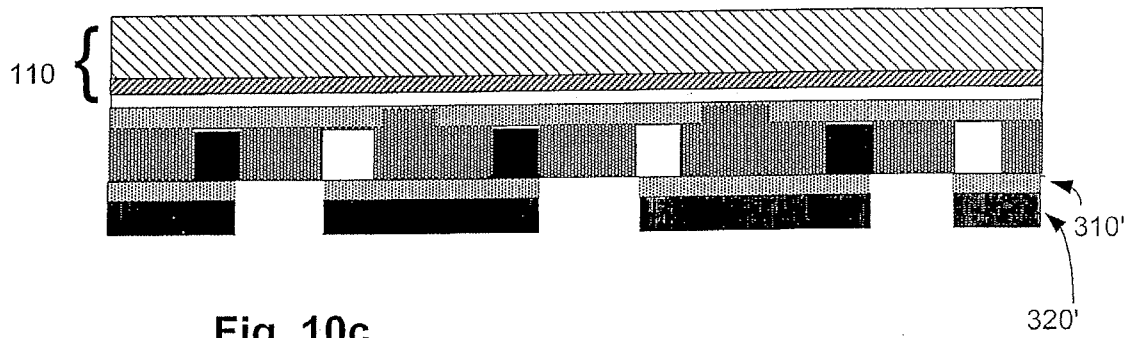


Fig. 10c

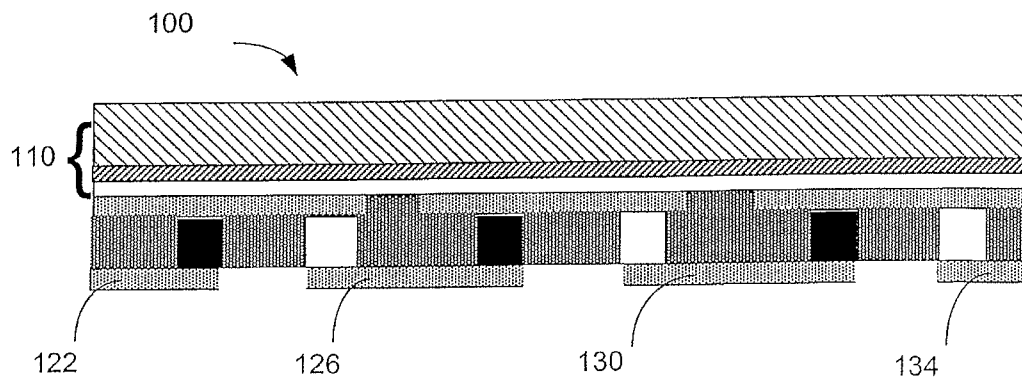
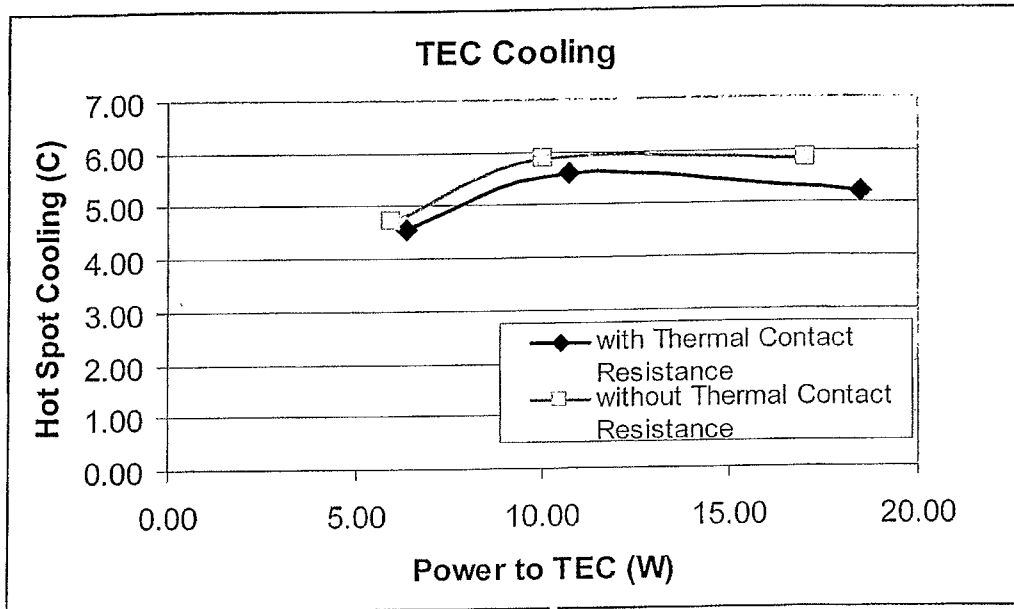
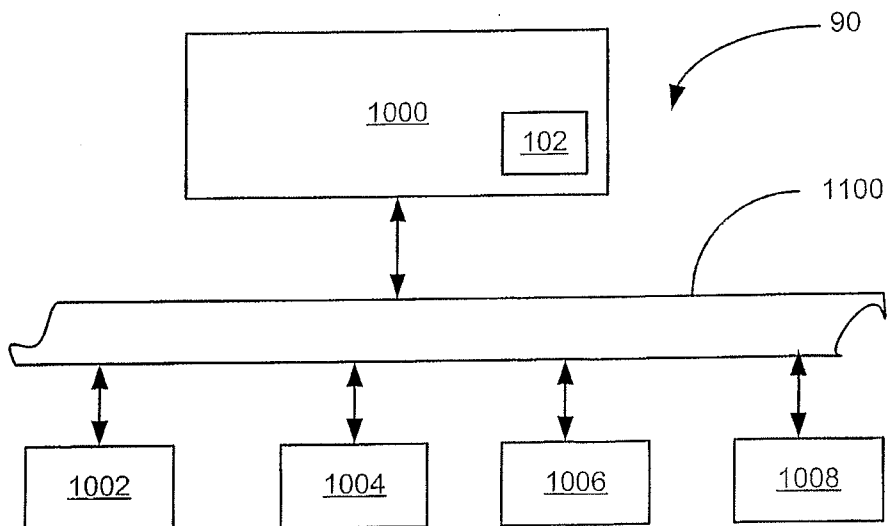


Fig. 10d

**Fig. 11****Fig. 12**